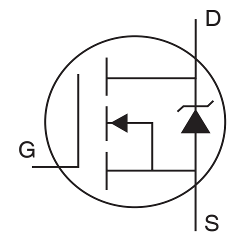
PD - 95130

International Rectifier

IRF540NSPbF
IRF540NLPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS} = 100V

$R_{DS(on)}$ = 44mΩ

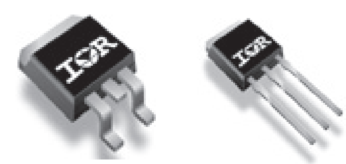
I_D = 33A

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D^2Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D^2Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF540NL) is available for low-profile applications.



D^2Pak IRF540NSPbF   TO-262 IRF540NLPbF

Absolute Maximum Ratings

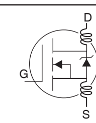
	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V ⑦	33	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V ⑦	23	
I_{DM}	Pulsed Drain Current ①⑦	110	
P_D @T_C = 25°C	Power Dissipation	130	W
	Linear Derating Factor	0.87	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current①	16	A
E_{AR}	Repetitive Avalanche Energy①	13	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑦	7.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

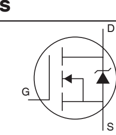
	Parameter	Typ.	Max.	Units
$R_{θJC}$	Junction-to-Case	–––	1.15	°C/W
$R_{θJA}$	Junction-to-Ambient (PCB mount)**	–––	40	

3/18/04

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.12	–––	V/°C	Reference to 25°C, I_D = 1mA ⑦
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	44	mΩ	V_{GS} = 10V, I_D = 16A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–––	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	21	–––	–––	S	V_{DS} = 50V, I_D = 16A④⑦
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	μA	V_{DS} = 100V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 80V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -20V
Q_g	Total Gate Charge	–––	–––	71	nC	I_D = 16A
Q_{gs}	Gate-to-Source Charge	–––	–––	14		V_{DS} = 80V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	21		V_{GS} = 10V, See Fig. 6 and 13 ④⑦
$t_{d(on)}$	Turn-On Delay Time	–––	11	–––	ns	V_{DD} = 50V
t_r	Rise Time	–––	35	–––		I_D = 16A
$t_{d(off)}$	Turn-Off Delay Time	–––	39	–––		R_G = 5.1Ω
t_f	Fall Time	–––	35	–––		V_{GS} = 10V, See Fig. 10 ④⑦
L_D	Internal Drain Inductance	–––	4.5	–––	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	–––	7.5	–––		
C_{iss}	Input Capacitance	–––	1960	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	250	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	40	–––		f = 1.0MHz, See Fig. 5 ⑦
E_{AS}	Single Pulse Avalanche Energy②⑦	–––	700⑤	185⑥	mJ	I_{AS} = 16A, L = 1.5mH

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	33	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)①	–––	–––	110		
V_{SD}	Diode Forward Voltage	–––	–––	1.2	V	T_J = 25°C, I_S = 16A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	115	170	ns	T_J = 25°C, I_F = 16A
Q_{rr}	Reverse Recovery Charge	–––	505	760	nC	di/dt = 100A/μs ④⑦
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L =1.5mH R_G = 25Ω, I_{AS} = 16A. (See Figure 12)

③ $I_{SD} \leq$ 16A, di/dt ≤ 340A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑤ This is a typical value at device destruction and represents operation outside rated limits.

⑥ This is a calculated value limited to T_J = 175°C .

⑦ Uses IRF540N data and test conditions.

**When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

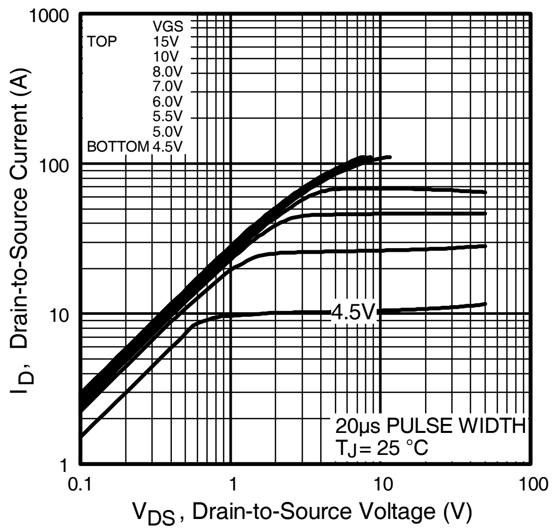


Fig 1. Typical Output Characteristics

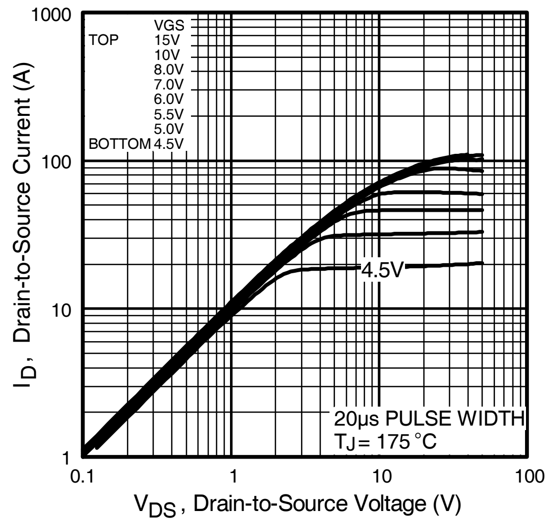


Fig 2. Typical Output Characteristics

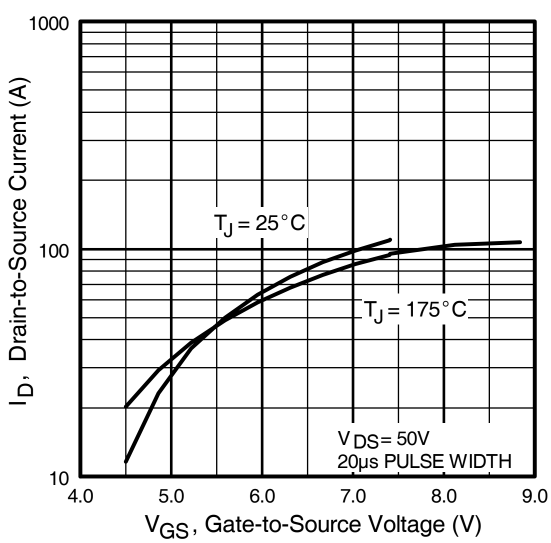


Fig 3. Typical Transfer Characteristics

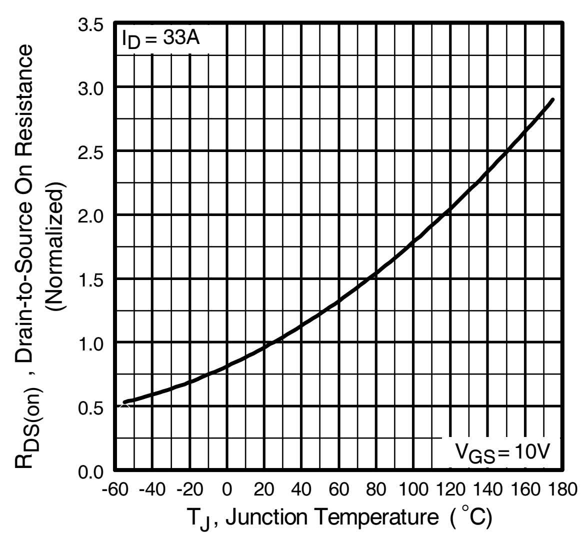


Fig 4. Normalized On-Resistance
Vs. Temperature

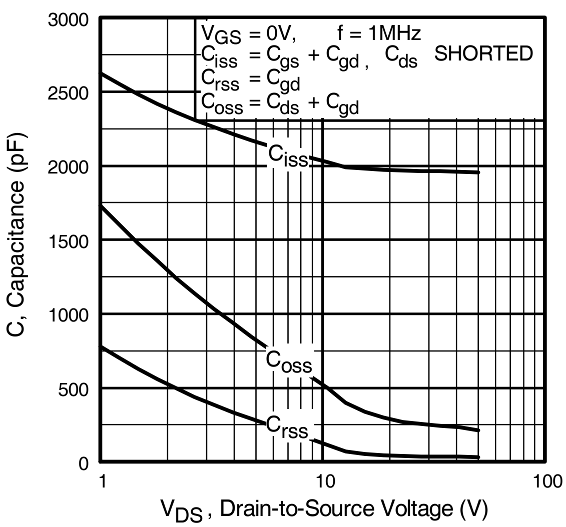


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

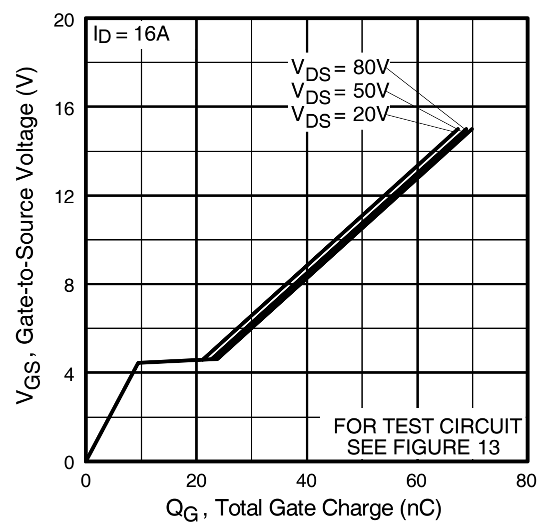


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

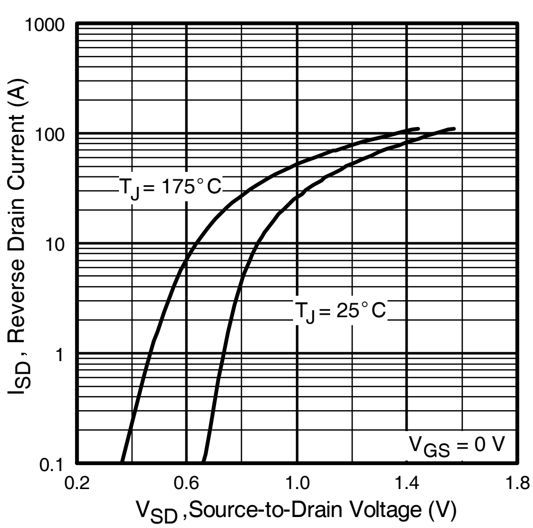


Fig 7. Typical Source-Drain Diode Forward Voltage

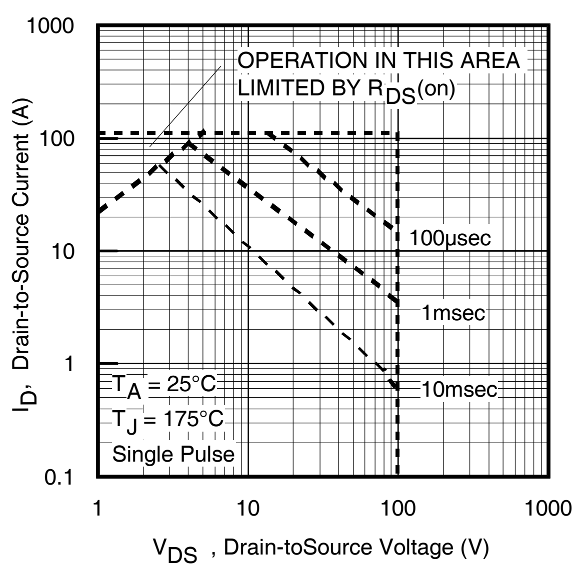


Fig 8. Maximum Safe Operating Area

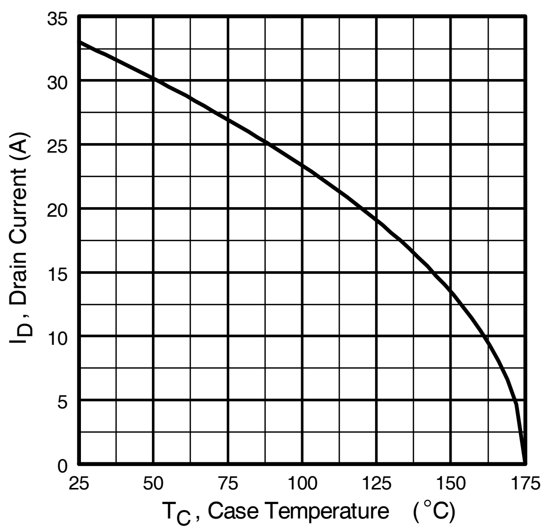


Fig 9. Maximum Drain Current Vs. Case Temperature

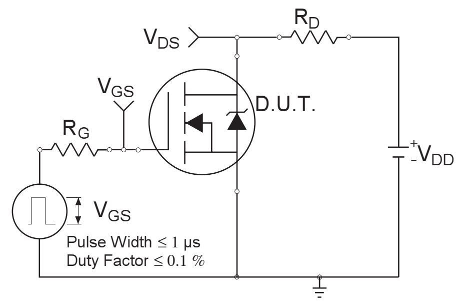


Fig 10a. Switching Time Test Circuit

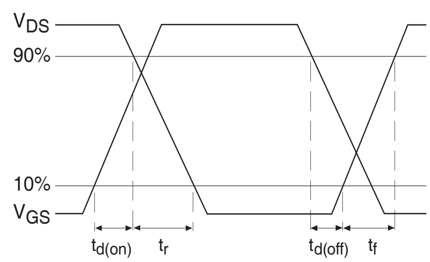


Fig 10b. Switching Time Waveforms

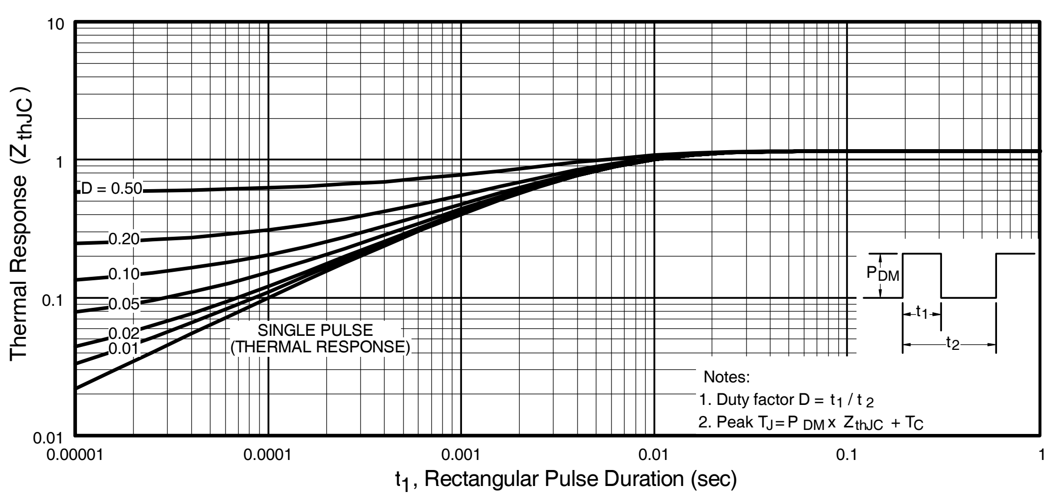


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

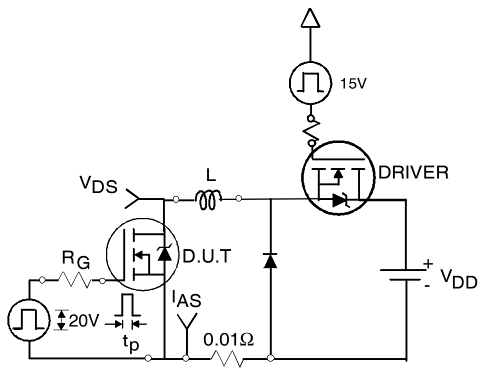


Fig 12a. Unclamped Inductive Test Circuit

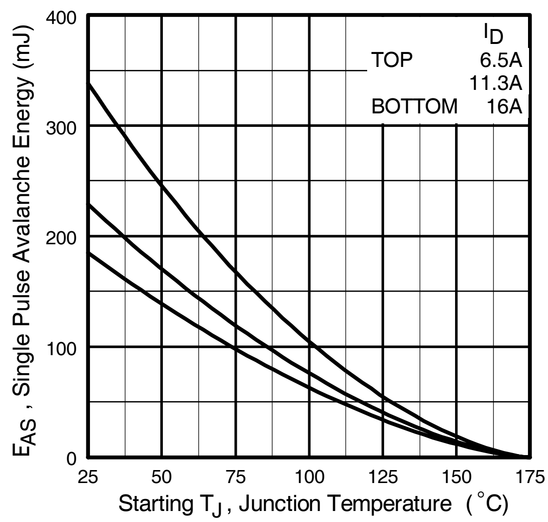


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

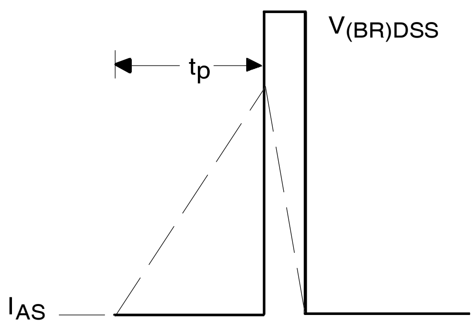


Fig 12b. Unclamped Inductive Waveforms

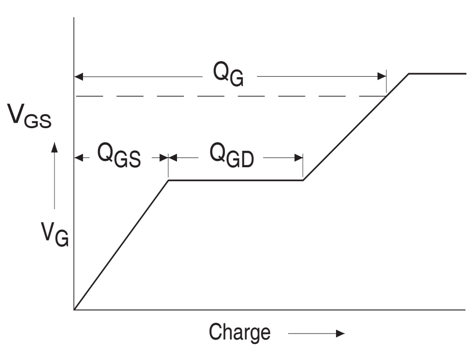


Fig 13a. Basic Gate Charge Waveform

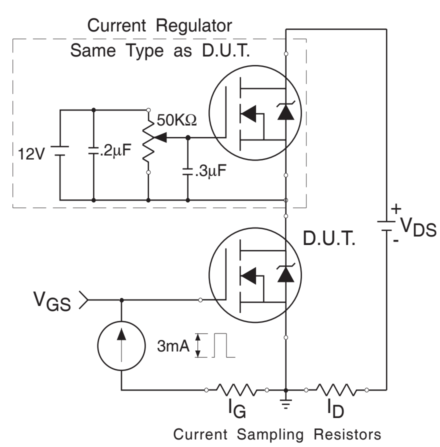
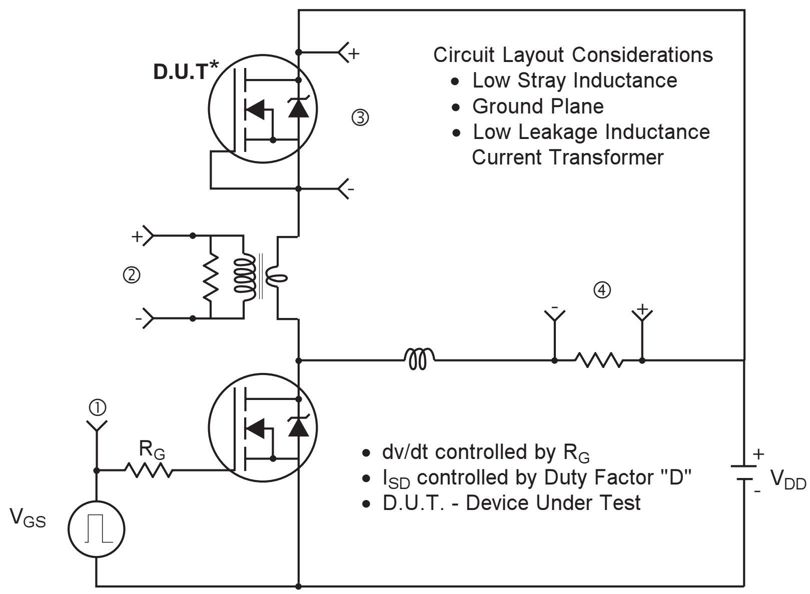
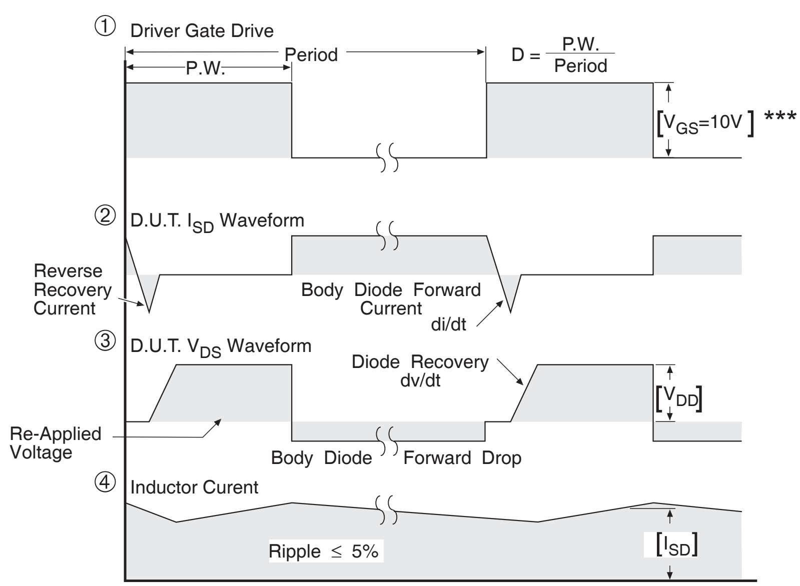


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel

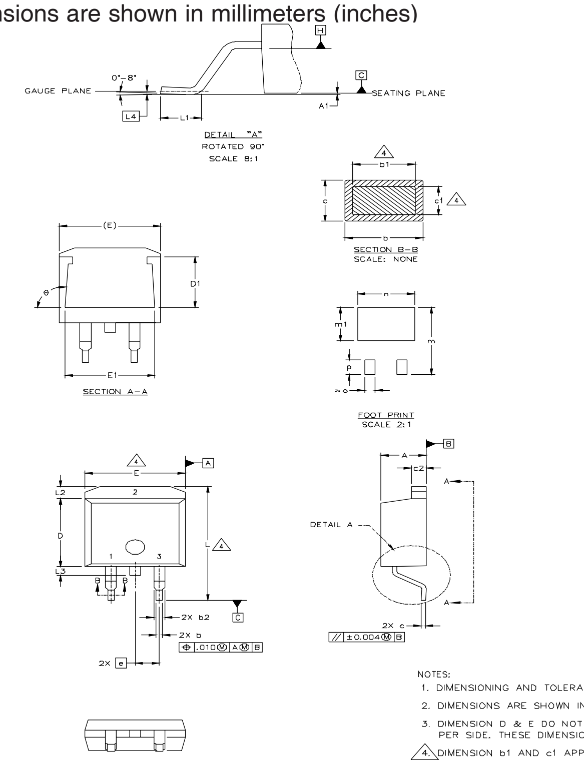


*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

Fig 14. For N-channel HEXFET® power MOSFETs

D^2Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

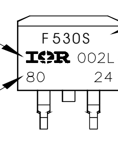
D^2Pak Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF530S WITH LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead-Free"

INTERNATIONAL RECTIFIER LOGO

ASSEMBLY LOT CODE



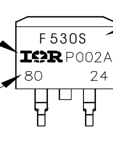
PART NUMBER

DATE CODE
YEAR 0 = 2000
WEEK 02
LINE L

OR

INTERNATIONAL RECTIFIER LOGO

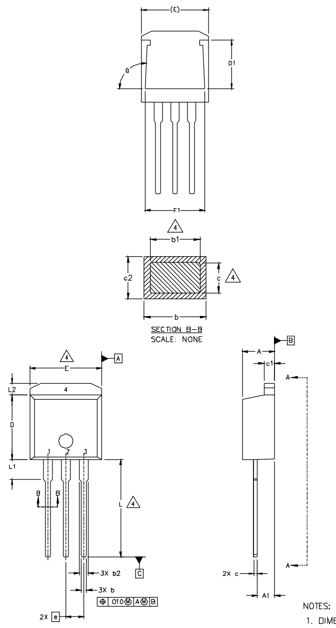
ASSEMBLY LOT CODE



PART NUMBER

DATE CODE
P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)
YEAR 0 = 2000
WEEK 02
A = ASSEMBLY SITE CODE

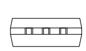
TO-262 Package Outline



SYMBOL	DIMENSIONS MILLIMETERS MIN.	MILLIMETERS MAX.	INCHES MIN.	INCHES MAX.	NOTES
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET	IGBT
1.– GATE	1- GATE
2.– DRAIN	2- COLLECTOR
3.– SOURCE	3- EMITTER
4.– DRAIN	



NOTES:

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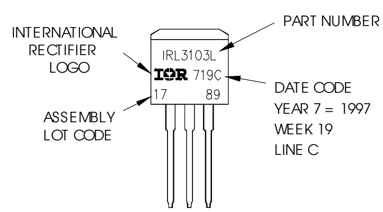
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

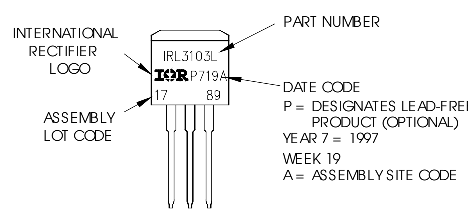
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

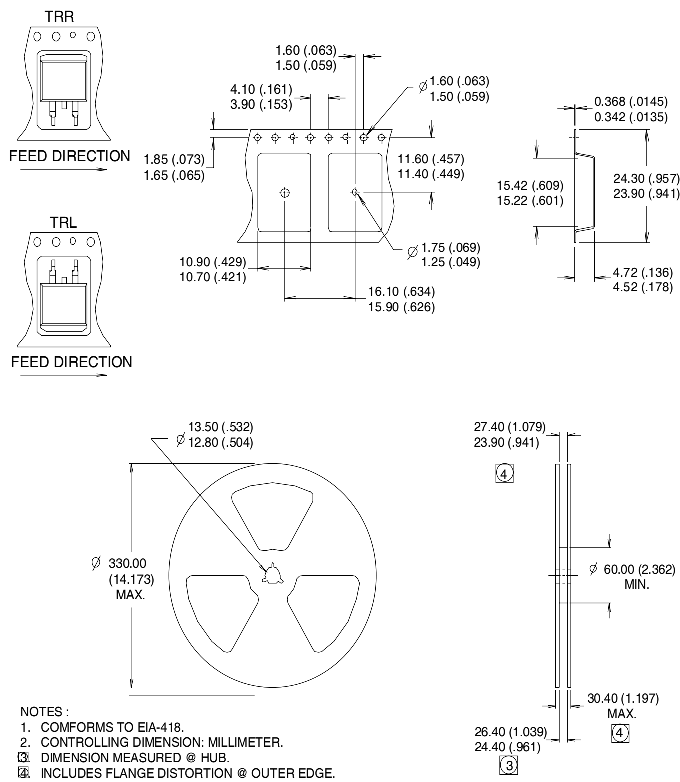


OR



D^2Pak Tape & Reel Infomation

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.03/04

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/

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- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.